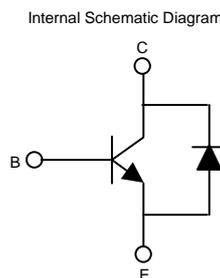
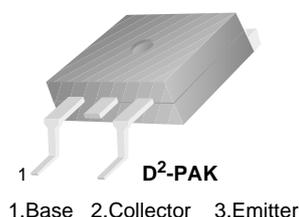


# FJB3307D

## High Voltage Fast Switching NPN Power Transistor

### Features

- Built-in Diode between Collector and Emitter
- Suitable for Electronic Ballast and Switch Mode Power Supplies



### Absolute Maximum Ratings $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	700	V
$V_{CEO}$	Collector-Emitter Voltage	400	V
$V_{EBO}$	Emitter-Base Voltage	9	V
$I_C$	Collector Current (DC)	8	A
$I_{CP}$	* Collector Current (Pulse)	16	A
$I_B$	Base Current (DC)	4	A
$I_{BP}$	* Base Current (Pulse)	8	A
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	-55 to 150	$^\circ\text{C}$

\* Pulse Test:  $PW = 300\mu\text{s}$ , Duty Cycle = 2% Pulsed

### Thermal Characteristics

Symbol	Parameter	Value	Units	
$P_D$	Total Device Dissipation	$T_a = 25^\circ\text{C}$	1.72	W
		$T_c = 25^\circ\text{C}$	80	W
$R_{\theta ja}$	Thermal Resistance, Junction to Ambient	72.5	$^\circ\text{C/W}$	
$R_{\theta jc}$	Thermal Resistance, Junction to Case	1.56	$^\circ\text{C/W}$	

**Electrical Characteristics**  $T_a = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = 500\mu\text{A}, I_E = 0$	700			V
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 5\text{mA}, I_B = 0$	400			V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = 500\mu\text{A}, I_C = 0$	9			V
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 9\text{V}, I_C = 0$			1	mA
$h_{FE1}$ $h_{FE2}$	DC Current Gain	$V_{CE} = 5\text{V}, I_C = 2\text{A}$ $V_{CE} = 5\text{V}, I_C = 5\text{A}$	8 5		40 30	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 2\text{A}, I_B = 0.4\text{A}$ $I_C = 5\text{A}, I_B = 1\text{A}$ $I_C = 5\text{A}, I_B = 1\text{A}, T_a = 100^\circ\text{C}$ $I_C = 8\text{A}, I_B = 2\text{A}$			1 2 3 3	V V V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 2\text{A}, I_B = 0.4\text{A}$ $I_C = 5\text{A}, I_B = 1\text{A}$ $I_C = 5\text{A}, I_B = 1\text{A}, T_a = 100^\circ\text{C}$			1.2 1.6 2	V V V
$V_F$	Diode Forward Voltage	$I_C = 3\text{A}$			2.5	V
$C_{ob}$	Output Capacitance	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		60		pF
$t_{STG}$	Storage Time	$V_{CC} = 125\text{V}, I_C = 5\text{A}$			3	$\mu\text{s}$
$t_F$	Fall Time	$I_{B1} = -I_{B2} = 1\text{A}, R_L = 50\Omega$			0.7	$\mu\text{s}$
$t_{STG}$	Storage Time	$V_{CC} = 30\text{V}, I_C = 5\text{A}, L = 200\mu\text{H}$ $I_{B1} = 1\text{A}, R_{BB} = 0\Omega,$			2.3	$\mu\text{s}$
$t_F$	Fall Time	$V_{BE(OFF)} = -5\text{V},$ $V_{CLAMP} = 250\text{V}$			150	ns

\* Pulse test:  $PW = 300\mu\text{s}$ , Duty Cycle = 2% Pulsed

**$h_{FE}$  Classification**

Classification	H1	H2
$h_{FE1}$	15 ~ 28	26 ~ 39

## Typical Performance Characteristics

Figure 1. Static Characteristic

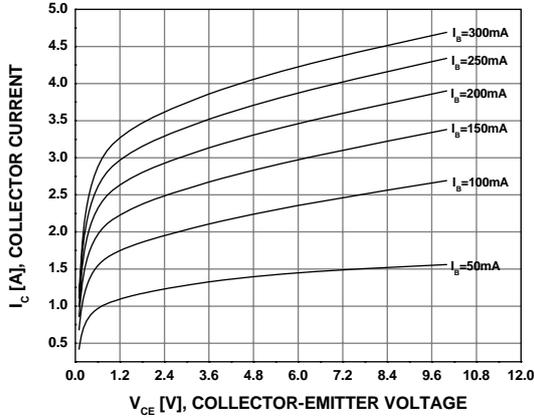


Figure 2. DC Current Gain

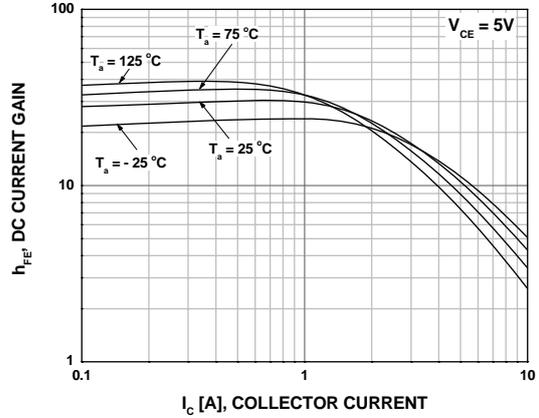


Figure 3. Collector-Emitter Saturation Voltage

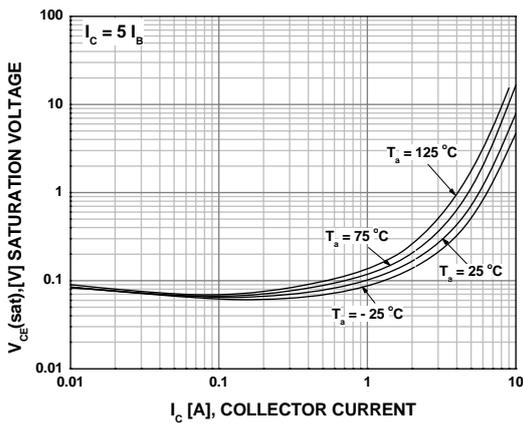


Figure 4. Base-Emitter Saturation Voltage

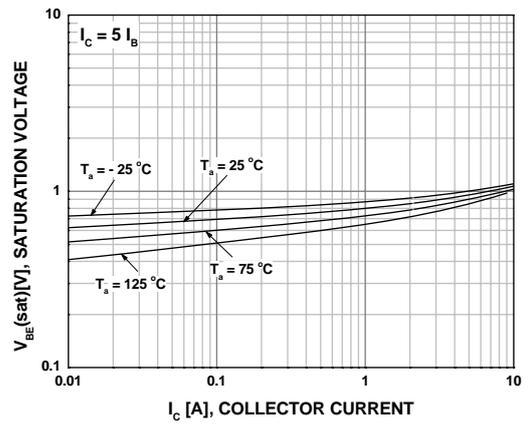


Figure 5. Collector Output Capacitance

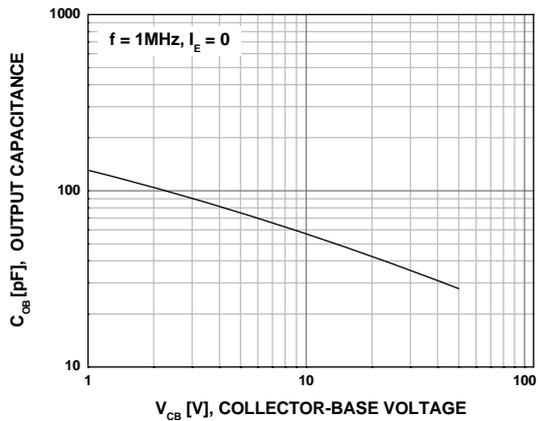
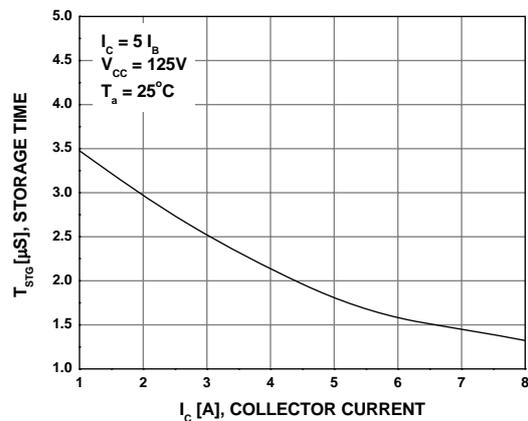
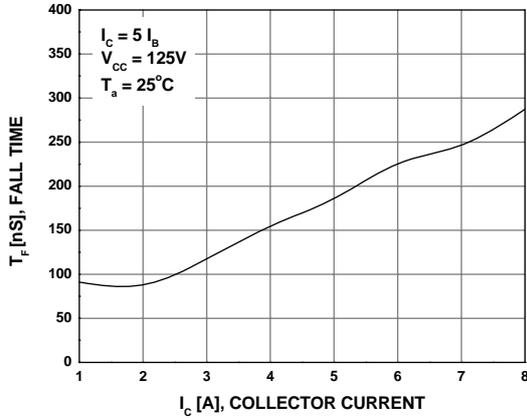


Figure 6. Storage Time (Resistive Load)

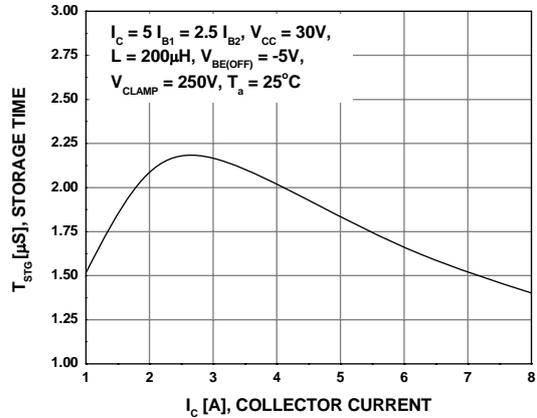


**Typical Performance Characteristics** (Continued)

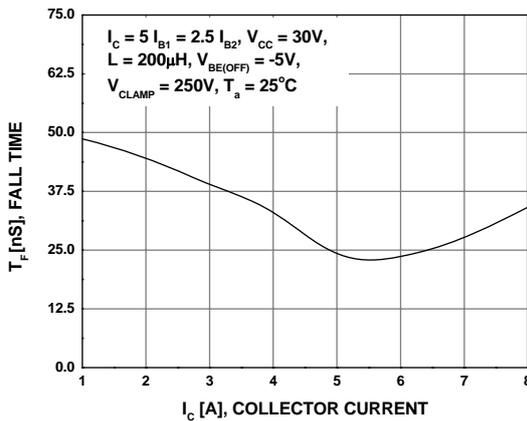
**Figure 7. Fall Time (Resistive Load)**



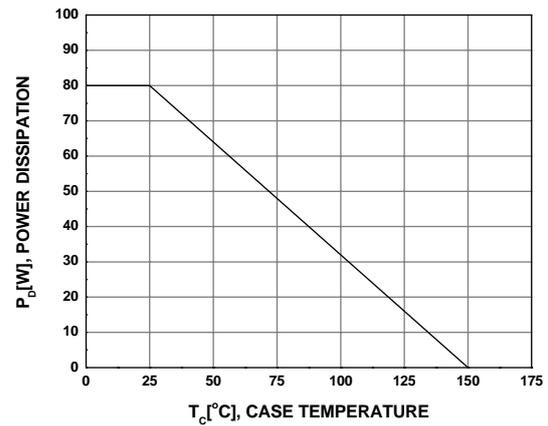
**Figure 8. Storage Time (Inductive Load)**



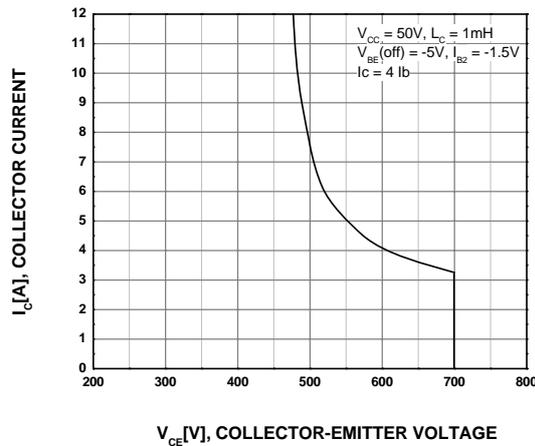
**Figure 9. Fall Time (Inductive Load)**



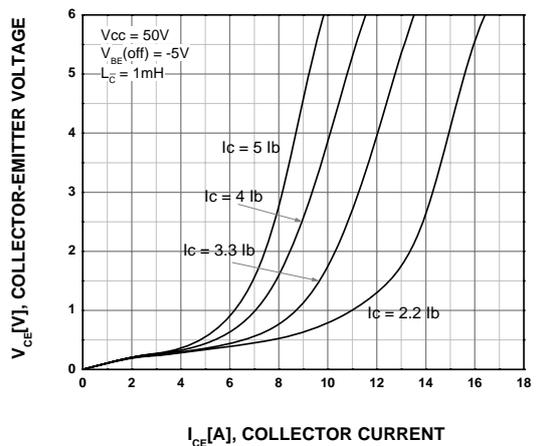
**Figure 10. Power Derating**



**Figure 11. Reverse Bias Safe Operating Area**

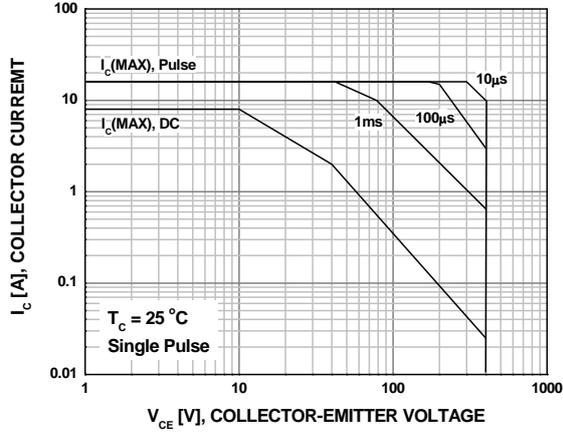


**Figure 12. RBSOA Saturation**



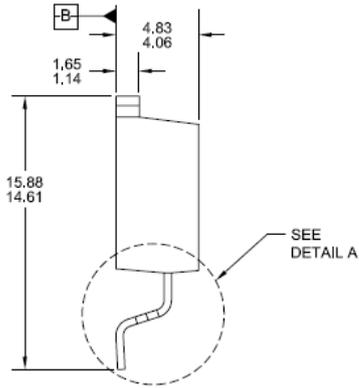
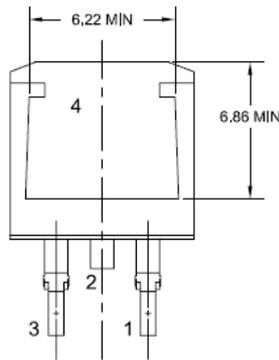
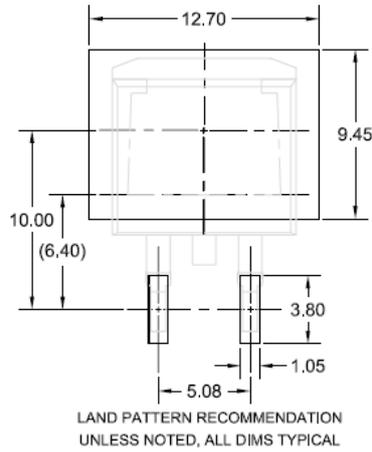
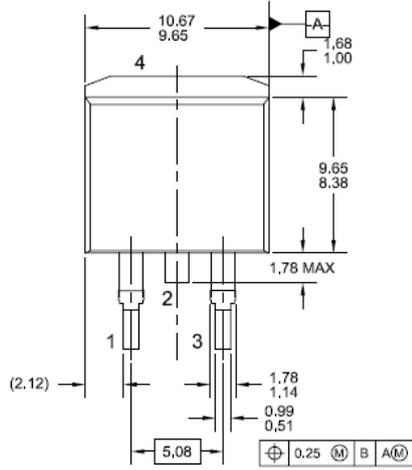
**Typical Performance Characteristics** (Continued)

**Figure 13. Forward Biased Safe Operating Area**

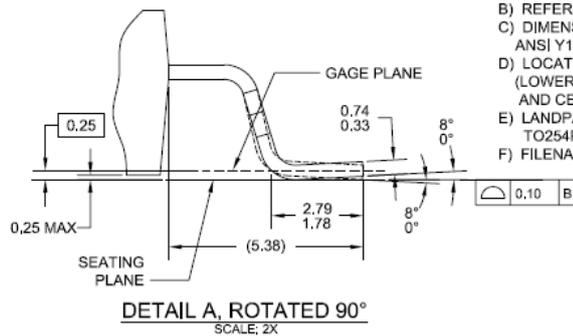


**Physical Dimensions**

**D<sup>2</sup>-PAK**



- NOTES: UNLESS OTHERWISE SPECIFIED  
 A) ALL DIMENSIONS ARE IN MILLIMETERS.  
 B) REFERENCE JEDEC, TO-263, VARIATION AB.  
 C) DIMENSIONING AND TOLERANCING PER ANSI Y14.5M - 1994.  
 D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).  
 E) LANDPATTERN RECOMMENDATION PER IPC TO254P1524X482-3N  
 F) FILENAME: TO263A02REV6



Dimensions in Millimeters



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| BitSiC™   | GreenBridge™                                   | QFET®   | TinyBuck™   |
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